



A Product Line of **Diodes Incorporated**



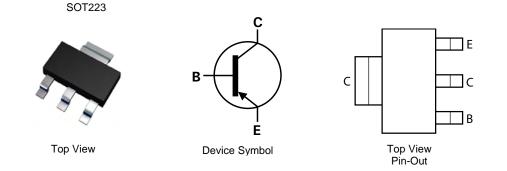
PNP SILICON PLANAR HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- $BV_{CEO} > 60V$ •
- Maximum continuous current $I_{C(cont)} = 3A$ •
- Low Saturation Voltage
- Complementary Type FZT651 •
- **RoHS Compliant** •
- Halogen and Antimony Free. "Green" Device (Note 1) •
- Qualified to AEC-Q101 Standards for High Reliability •

Mechanical Data

- Case: SOT223 •
- UL Flammability Rating 94V-0 •
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)

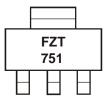


Ordering Information (Note 2)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT751TA	FZT751	7	12	1,000
FZT751TC	FZT751	13	12	4,000

Notes: 1. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com 2. For Packaging Details, go to our website at http://www.diodes.com.

Marking Information



FZT751 = Product Type Marking Code





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-3	A
Peak Pulse Current	I _{CM}	-6	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

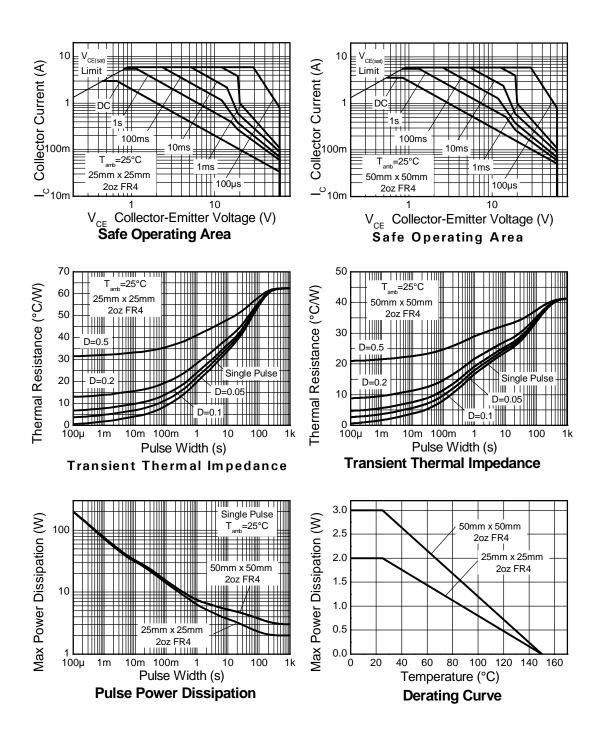
Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 3)	D	2	W
	(Note 4)	PD	3	W
Thermal Resistance, Junction to Ambient	(Note 3)	D	62.5	°C/W
mermai Resistance, Junction to Ambient	(Note 4)	R _{θJA}	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 5)		R _{θJL}	12.93	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

 For devices mounted on 25mm x 25mm single sided 2oz weight copper, in still air conditions.
For devices mounted on 50mm x 50mm single sided 2oz weight copper, in still air conditions.
Thermal resistance from junction to solder-point (at the end of the collector lead) Notes:





Thermal Characteristics







Electrical Characteristics @T_A = 25°C unless otherwise specified

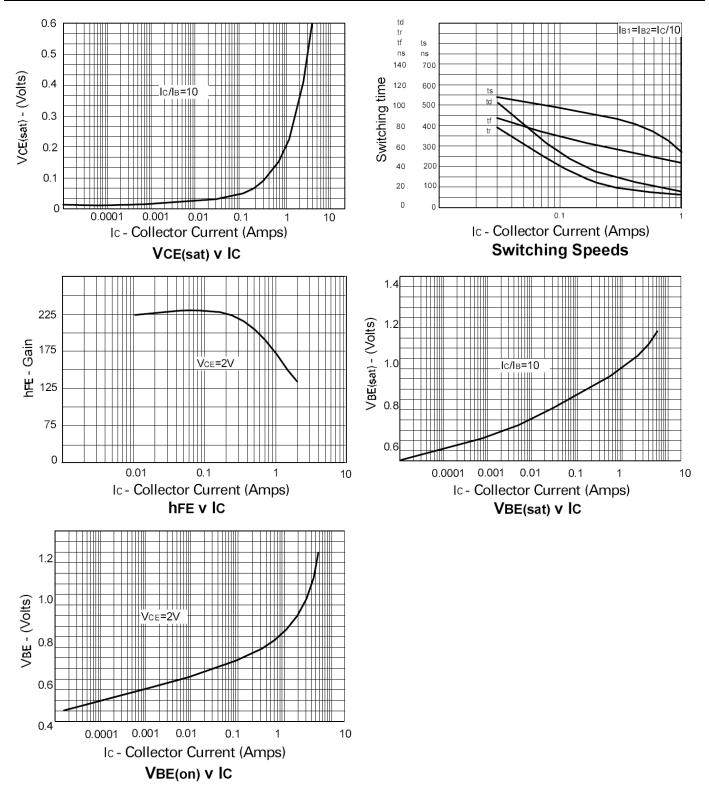
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-80		_	V	$I_{\rm C} = -100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	-60	-	-	V	$I_{\rm C} = -10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-	-	V	I _E = -100μA
Collector Cut-off Current	I _{CBO}	-	-	-0.1	μA	$V_{CB} = -60V$
		-	-	-10		$V_{CB} = -60V, T_{amb} = 100^{\circ}C$
Emitter Cut-off Current	I _{EBO}	-	-	-0.1	μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage (Note 6)	N	-	-0.15	-0.3	V	$I_{C} = -1A, I_{B} = -100mA$
	V _{CE(sat)}	-	-0.45	-0.6		$I_{C} = -3A, I_{B} = -300mA$
Base-Emitter Saturation Voltage (Note 6)	V _{CE(sat)}	-	-0.9	-1.25	V	$I_{\rm C} = -1A, I_{\rm B} = -100 {\rm mA}$
Base-Emitter Turn-On Voltage (Note 6)	V _{BE(on)}	-	-0.8	-1.0	V	$I_{C} = -1A, V_{CE} = -2V$
	hFE	70	200	-	_	I _C = -50mA, V _{CE} = -2V
DC Current Gain (Note 6)		100	200	300		$I_{C} = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 6)		80	170	-		$I_{C} = -1A, V_{CE} = -2V$
		40	150	-		$I_{C} = -2A, V_{CE} = -2V$
Current Gain-Bandwidth Product (Note 6)	fт	100	140	-	MHz	$V_{CE} = -5V, I_C = -100mA$ f = 100MHz
Turn-On Time	t _{on}	_	40	_	ns	$V_{CC} = -10V, I_{C} = -500mA$
Turn-Off Time	t _{off}	-	450	_	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Output Capacitance (Note 6)	C _{obo}		-	30	pF	$V_{CB} = -10V, f = 1MHz$

6. Measured under pulsed conditions. Pulse width \leq 300 $\mu s.$ Duty cycle \leq 2% Notes:





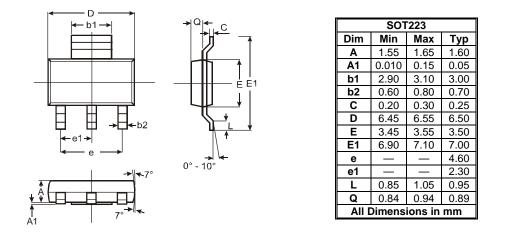
Typical Characteristics



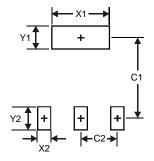




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3





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